MOSFET - Power, Single N-Channel, Small Signal 20 V, 220 mA

NTNSOK8N021Z

Features

- Low Profile Ultra Small Package, XDFN3 (0.62 x 0.42 x 0.4 mm) for Extremely Space–Constrained Applications
- 1.5 V Gate Drive
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- Small Signal Load Switch
- High Speed Interfacing
- Level Shift

MAXIMUM RATINGS (T_J = 25°C unless otherwise stated)

Parameter			Symbol	Value	Unit
Drain-to-Source Voltage			V _{DSS}	20	V
Gate-to-Source Voltage			V _{GS}	±8	V
Continuous Drain	Steady T _A = 25°C		I _D	220	mA
Current (Note 1)	State	T _A = 85°C		158	
	t ≤ 5 s	T _A = 25°C		253	
Power Dissipation (Note 1)	Steady State	T _A = 25°C	P _D	125	mW
	t ≤ 5 s			166	
Pulsed Drain Current	t _p = 10 μs		I _{DM}	846	mA
Operating Junction and Storage Temperature Range			T_J , T_{STG}	–55 to 150	°C
Source Current (Body Diode) (Note 2)			Is	200	mA
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			TL	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- Surface-mounted on FR4 board using the minimum recommended pad size, or 2 mm², 1 oz Cu.
- 2. Pulse Test: pulse width $\leq 300~\mu s,~duty~cycle \leq 2\%$

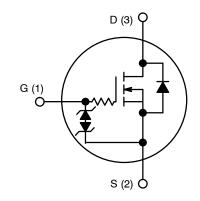


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V _{(BR)DSS}	R _{DS(on)} MAX	I _D Max
	1.5 Ω @ 4.5 V	
20 V	3.3 Ω @ 1.8 V	220 mA
	8.0 Ω @ 1.2 V	

N-CHANNEL MOSFET



MARKING DIAGRAM





XDFN3 CASE 711BH

= Specific Device Code

M = Date Code

ORDERING INFORMATION

Device	Package	Shipping [†]
NTNS0K8N021ZTC0	XDFN3 (Pb-Free)	8000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

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THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Ambient - Steady State (Note 3)	$R_{\theta JA}$	998	°C/W
Junction-to-Ambient - t ≤ 5 s (Note 3)	$R_{\theta JA}$	751	C/VV

^{3.} Surface–mounted on FR4 board using the minimum recommended pad size, or 2 mm², 1 oz Cu.

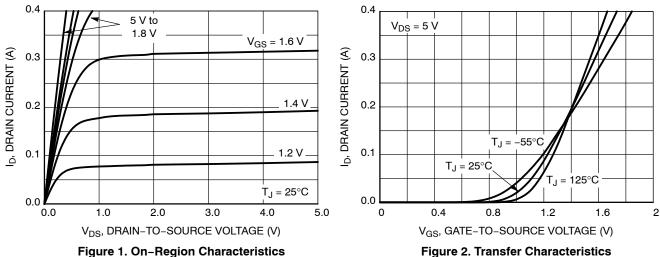
ELECTRICAL CHARACTERISTICS ($T_J = 25^{\circ}C$ unless otherwise stated)

Parameter	Symbol	Test Condition		Min	Тур	Max	Unit	
OFF CHARACTERISTICS					-	•		
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		20			V	
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V, V _{DS} = 5 V	T _J = 25°C			50	nA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V, V _{DS} = 16 V	T _J = 25°C			100	nA	
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS} =	±5 V			±100	nA	
ON CHARACTERISTICS (Note 4)								
Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = 2	$V_{GS} = V_{DS}, I_D = 250 \mu A$			1.0	V	
Drain-to-Source On Resistance		$V_{GS} = 4.5 \text{ V}, I_D = 1$	00 mA		0.8	1.5		
	R _{DS(on)}	$V_{GS} = 1.8 \text{ V}, I_D = 20 \text{ mA}$			1.4	3.0	Ω	
		V _{GS} = 1.2 V, I _D = 10 mA			3.2	8.0		
Forward Transconductance	9 _{FS}	$V_{DS} = 5 \text{ V, I}_{D} = 125 \text{ mA}$			0.48		S	
Source-Drain Diode Voltage	V_{SD}	V _{GS} = 0 V, I _S = 10 mA			0.6	1.0	V	
CHARGES & CAPACITANCES								
Input Capacitance	C _{ISS}				12.3			
Output Capacitance	C _{OSS}	V _{GS} = 0 V, freq = 1 MHz	$V_{GS} = 0 \text{ V}$, freq = 1 MHz, $V_{DS} = 15 \text{ V}$		3.4		pF	
Reverse Transfer Capacitance	C _{RSS}				2.5			
SWITCHING CHARACTERISTICS, VGS = 4.5 V (Note 4)								
Turn-On Delay Time	t _{d(ON)}	$V_{GS} = 4.5 \text{ V}, V_{DD} = 15 \text{ V},$ $I_{D} = 200 \text{ mA}, R_{G} = 2 \Omega$			16.5			
Rise Time	t _r				25.5		1	
Turn-Off Delay Time	t _{d(OFF)}				142		ns	
Fall Time	t _f				80			

^{4.} Switching characteristics are independent of operating junction temperatures

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TYPICAL CHARACTERISTICS



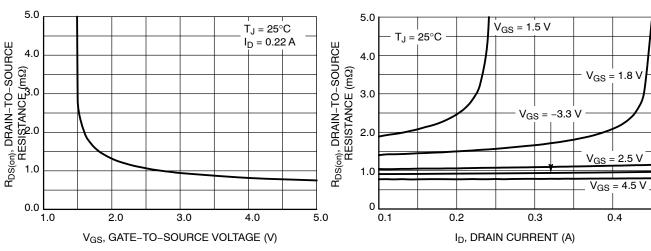


Figure 3. On-Resistance vs. Gate-to-Source Voltage

Figure 4. On-Resistance vs. Drain Current and **Gate Voltage**

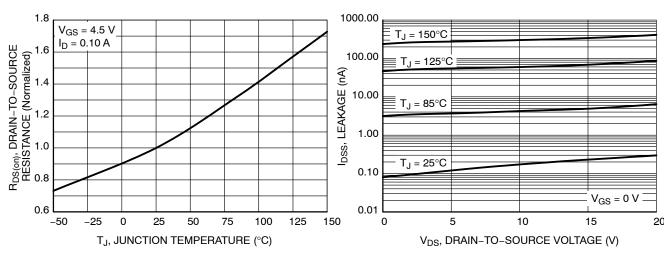


Figure 5. On-Resistance Variation with **Temperature**

Figure 6. Drain-to-Source Leakage Current vs. Voltage

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TYPICAL CHARACTERISTICS

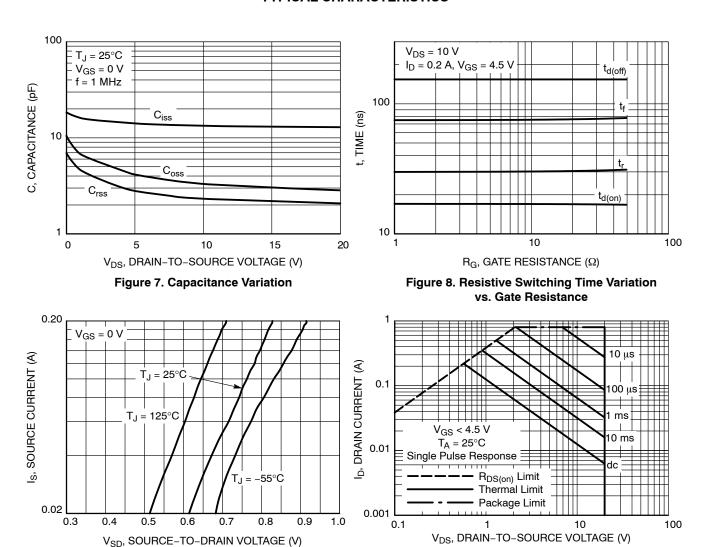
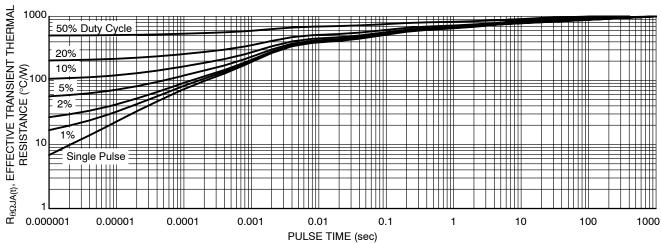


Figure 9. Diode Forward Voltage vs. Current

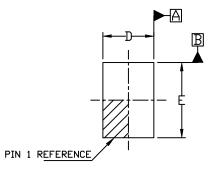
Figure 10. Maximum Rated Forward Biased Safe Operating Area

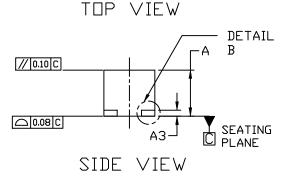




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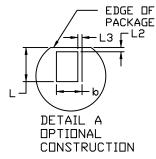






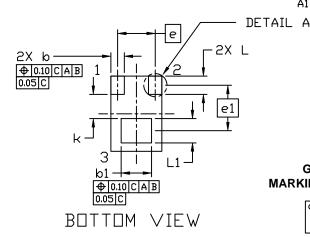
NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
- CONTROLLING DIMENSION: MILLIMETERS
- DIMENSION 6 AND 61 APPLIES TO THE PLATED TERMINALS AND IS MEASURED BETWEEN 0.20 AND 0.25 FROM THE TERMINAL TIP.
- COPLANARITY APPLIES TO THE PLATED TERMINALS.



EXPOSED COPPER
MOLDING COMPOUND
DETAIL B A1 OPTIONAL CONSTRUCTION

	LIES TO THE TENTED TENTINALS.					
MILLIMETERS						
MIN.	N□M.	MAX.				
0.33	0.38	0.43				
		0.07				
(.13 REF					
0.05	0.11	0.17				
0.20	0.25	0.30				
0.32	0.42	0.52				
0.52	0.62	0.72				
0.30 BSC						
0.38 BCC						
0.09	0.15	0.21				
0.15	0.20	0.25				
		0.03				
		0.03				
0.20 REF						
	MIN. 0.33 0.05 0.20 0.32 0.52 0.52 0.09 0.15	MIN. NIM. 0.33 0.38 0.13 REF 0.05 0.11 0.20 0.25 0.32 0.42 0.52 0.62 0.30 BSC 0.38 BSC 0.38 BSC 0.09 0.15 0.15 0.20				



GENERIC MARKING DIAGRAM*



= Specific Device Code = Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G", may not follow the Generic Marking.

PACKAGE DUTLINE		− 0.35
0.29	ļ <u> </u>	0.30
0.11		2X 0.25
2X 0.21 0.52	╅┩╵╸┤	0.31 PITCH
	MMEN]	DED

MOUNTING FOOTPRINT

or not be present. Some products may

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DESCRIPTION:	XDFN3 0.42x0.62, 0.3P		PAGE 1 OF 1	

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